

AMENDMENTS TO THE SPECIFICATION

Please insert the following paragraph between the paragraph beginning at line 7 on page 10 and the paragraph beginning at line 21 on page 10:

B1

In particular, Figures 5 and 6 show that, in one embodiment, each FEM gate unit 32 overlies the source 16 and the drain 18 such that the FEM gate unit is vertically positioned over relatively more of the respective drain than the source, thereby defining asymmetric source and drain regions in each memory cell. Thus, in each memory cell the drain region is relatively larger than the respective source region. The relative size difference between the source and drain regions is caused at least in part by the fact that the source 16 is shared by adjacent FEM cells 50, as already discussed above. Such a source and drain structure desirably improves the drain-side coupling discussed herein.

new matter